## FIELD EFFECT TRANSISTOR (FET)

1.	Fie	id effect transistor (FET) operates on				
	a.	Majority carriers only				
	b.	Minority carries only				
	c.	Positive charged ions only				
	d.	On both majority and minority carriers				
2.	An FET is					
	a.	Unipolar transistor	c.	Tri-polar transistor		
	b.	Bipolar transistor	d.	None of these		
3.	An	FET is characterised by				
	a.	Current gain	c.	Power gain		
	b.	Voltage gain	d.	None of these		
		ATECTLIC		1		
4.	The	input impedance of an FET is of the order of		V CAM		
	a.	10 <sup>20</sup> ohm	c.	Hundred ohms		
	b.	Hundreds of mega ohm	d.	A few ohm		
5.	In F	ET .				
	a.	Its source and drain terminals are interchangeable	e			
	b. Its source and drain terminals are not interchangeable					
	c.	Its drain terminal is marked				

6. The noise level in FET is

d. None of these

- a. More than BJT
- b. Negligibly small

- c. less than BJT
- d. None of these
- 7. N-channel FETs are superior to P-channel FETs because
  - a. They have higher input impedance
  - b. They have higher switching time
  - c. They consume less power
  - d. Mobility of electrons is greater than holes

- 8. When a reverse bias is applied to gate of JFET the depletion region width
  - a. Is uniform in the channel
  - b. Is wider near the source and tapers near the drain
  - c. Is wider near the drain and tapers near source
  - d. None of the above
- 9. In an FET
  - a. one junction is reverse biased and the other forward biased
  - b. both the junctions are reverse biased
  - c. one junction has reverse bias on both sides of the junction
  - d. one junction has reverse bias on both side and forward bias on the other
- 10. Pinch-off voltage in a JFET is
  - a. the drain voltage that gives zero drain current
  - b. the gate to source voltage that gives unity drain current
  - c. the gate to source voltage that gives zero drain current
  - d. the drain voltage that gives infinite drain current
- 11. which of the following is the fastest switching device
  - a. JFET c. MOSFET
  - b. BJT d. Triode
- 12. FET is advantageous in comparison with BJT because of
  - a. High input impedance
  - b. Low noise
  - c. High gain-bandwidth product
  - d. Its current controlled behaviour
- 13. Which of the following statement is not true in case of FET?
  - a. It has high input impedance
  - b. It is less noisy than bipolar transistor
  - c. It has large gain-bandwidth product
  - d. All of the above

14.	. In a JFET, if the gate voltage $V_{\text{gs}}$ is made more negative, then				
	a.	Channel conductivity increases			
	b.	Depletion region decreases			
	c.	Channel conductivity decreases			

- d. Channel current increases
- 15. For a JEFT, when  $V_{DS}$  is increased beyond the pinch-off voltage, the drain current
  - a. increased
  - b. decreases
  - c. remains constant
  - d. first increased and then decreases
- 16. The gate controls
  - a. The width of the channel
  - b. The drain current

- c. The gate voltage
- d. All the above
- 17. When the drain saturation current is less than  $I_{DSS}$  a JFET acts like a
  - a. Bipolar junction transistor
- b. Current source
  - c. Resistor
  - d. Battery

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- 18. The pinch off voltage of a JFET is 5.0 volts. Its cut off voltage is

a. 
$$(5.0)^{1/2}$$
 V

d. 
$$(5.0)^{3/2}$$
 V

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- 19. A JFET has disadvantage of
  - a. being noisy
  - b. having small gain-bandwidth product
  - c. possessing positive temperature coefficient
  - d. having low input impedance
- 20. In a JFET, the primary control on drain current is exerted by
  - a. channel resistance
  - b. size of depletion regions
  - c. voltage drop across channel
  - d. gate reverse bias

## **Answers**

13.

(c)

2. 3. (b) 1. (a) (a) (b) 4. 5. (a) 6. (c) No junctions are present like BJT

7. (d) 8. (c) (c) 10. (c) 11. (c) 12. (a) 14, (c)

15. (c) 16. (a) 17. (c)

18. (c) Pinch off voltage is same as cut-off voltage 19. (b)

20. (d)

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